

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

2SC5466

DYNAMIC FOCUS APPLICATIONS

HIGH VOLTAGE SWITCHING APPLICATIONS

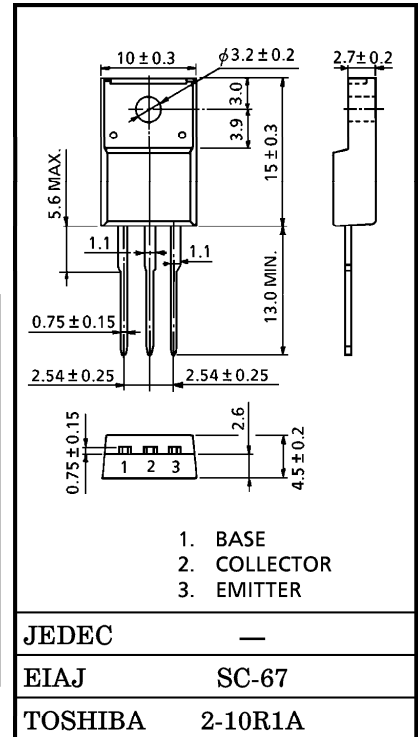
HIGH VOLTAGE AMPLIFIER APPLICATIONS

- High Voltage : $V_{CEO} = 800\text{ V}$

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	800	V
Collector-Emitter Voltage	V_{CEO}	800	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	50	mA
Base Current	I_B	25	mA
Collector Power Dissipation	P_C	$T_a = 25^\circ\text{C}$ 2.0	W
		$T_c = 25^\circ\text{C}$ 10	
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$

Unit in mm



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Weight : 1.7 g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 640\text{ V}, I_E = 0$	—	—	1.0	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	10	μA
DC Current Gain	h_{FE}	$V_{CE} = 5\text{ V}, I_C = 7\text{ mA}$	15	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 20\text{ mA}, I_B = 4\text{ mA}$	—	—	1.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 20\text{ mA}, I_B = 4\text{ mA}$	—	—	1.5	V
Transition Frequency	f_T	$V_{CE} = 10\text{ V}, I_C = 3\text{ mA}$	—	5.5	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 100\text{ V}, f = 1\text{ MHz}$	—	2.2	—	pF

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